



HE8551

PNP SILICON TRANSISTOR

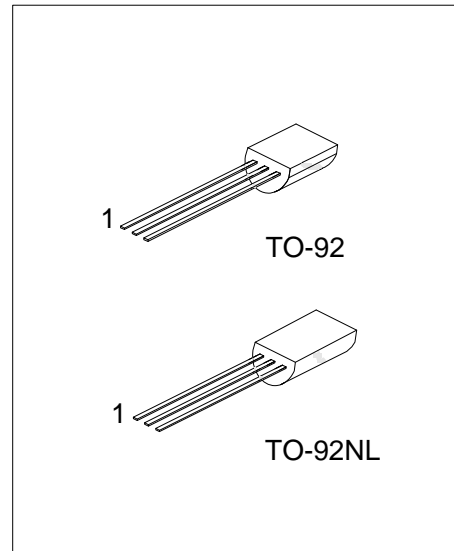
LOW VOLTAGE HIGH CURRENT SMALL SIGNAL PNP TRANSISTOR

DESCRIPTION

The UTC **HE8551** is a low voltage high current small signal PNP transistor, designed for Class B push-pull 2W audio amplifier for portable radio and general purpose applications.

FEATURES

- * Collector current up to 1.5A
- * Collector-emitter voltage up to 25 V
- * Complimentary to UTC **HE8051**



Lead-free: HE8551L

Halogen-free: HE8551G

ORDERING INFORMATION

Ordering Number			Package	Pin Assignment			Packing
Normal	Lead Free Plating	Halogen Free		1	2	3	
HE8551-x-T92-B	HE8551L-x-T92-B	HE8551G-x-T92-B	TO-92	E	B	C	Tape Box
HE8551-x-T92-K	HE8551L-x-T92-K	HE8551G-x-T92-K	TO-92	E	B	C	Bulk
HE8551-x-T9N-B	HE8551L-x-T9N-B	HE8551G-x-T9N-B	TO-92NL	E	B	C	Tape Box
HE8551-x-T9N-K	HE8551L-x-T9N-K	HE8551G-x-T9N-K	TO-92NL	E	B	C	Bulk

<p>HE8551L-x-T92-B</p> <p>(1)Packing Type (2)Package Type (3)Rank (4)Lead Plating</p>	<p>(1) B: Tape Box, K: Bulk (2) T92: TO-92, T9N: TO-92NL (3) x: refer to Classification of h_{FE2} (4) G: Halogen Free, L: Lead Free, Blank: Pb/Sn</p>
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■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-Base Voltage	V _{CBO}	-40	V
Collector-Emitter Voltage	V _{CEO}	-25	V
Emitter-Base Voltage	V _{EBO}	-6	V
Collector Dissipation (Ta=25°C)	P _C	1	W
Collector Current	I _C	-1.5	A
Junction Temperature	T _J	+150	°C
Storage Temperature	T _{STG}	-65 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

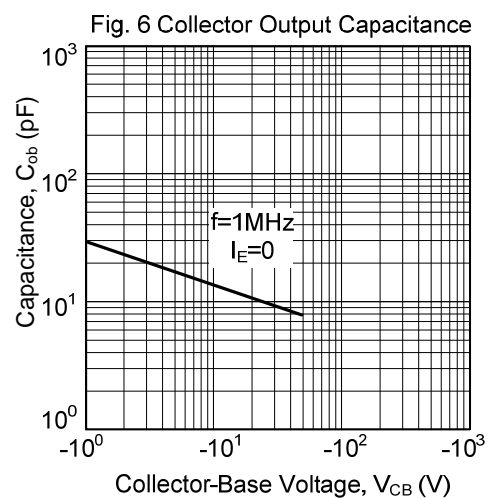
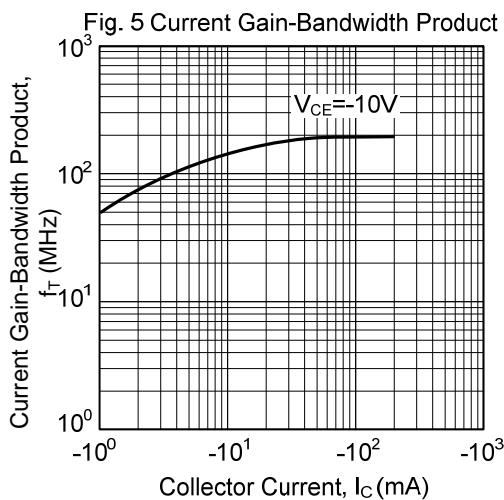
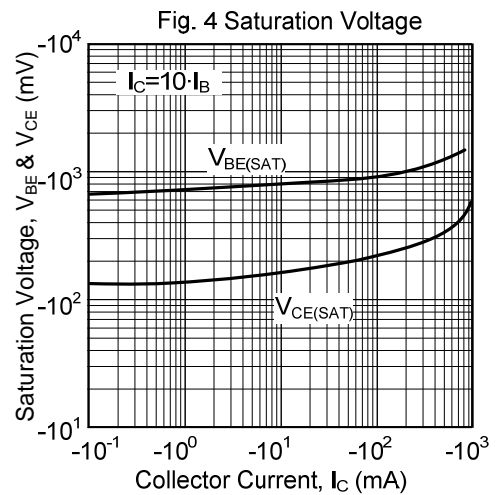
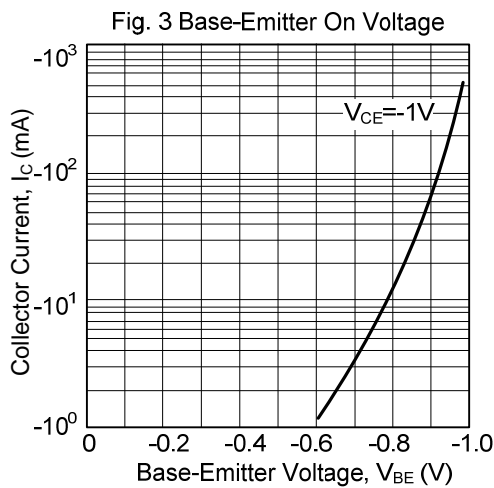
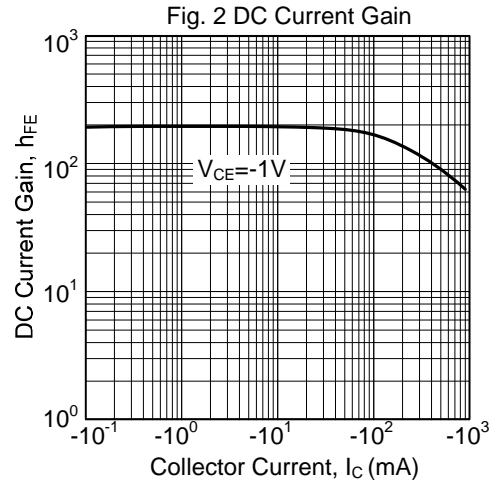
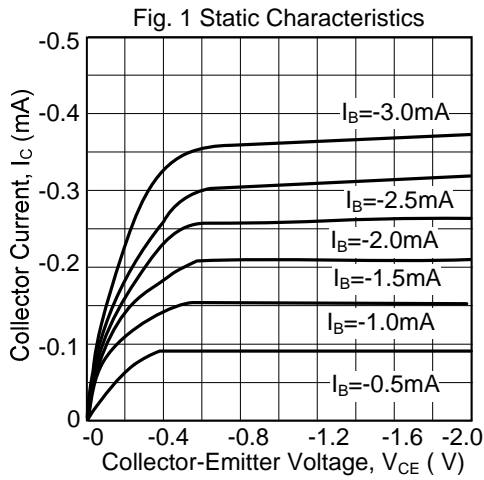
■ ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV _{CBO}	I _C =-100μA, I _E =0	-40			V
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _C =-2mA, I _B =0	-25			V
Emitter-Base Breakdown Voltage	BV _{EBO}	I _E =-100μA, I _C =0	-6			V
Collector Cut-Off Current	I _{CBO}	V _{CB} =-35V, I _E =0			-100	nA
Emitter Cut-Off Current	I _{EBO}	V _{EB} =-6V, I _C =0			-100	nA
DC Current Gain	h _{FE1}	V _{CE} =-1V, I _C =-5mA	45	170		
	h _{FE2}	V _{CE} =-1V, I _C =-100mA	85	160	500	
	h _{FE3}	V _{CE} =-1V, I _C =-800mA	40	80		
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	I _C =-800mA, I _B =-80mA		-0.28	-0.5	V
Base-Emitter Saturation Voltage	V _{BE(SAT)}	I _C =-800mA, I _B =-80mA		-0.98	-1.2	V
Base-Emitter Voltage	V _{BE}	V _{CE} =-1V, I _C =-10mA		-0.66	-1.0	V
Current Gain Bandwidth Product	f _T	V _{CE} =-10V, I _C =-50mA	100	190		MHz
Output Capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz		9.0		pF

■ CLASSIFICATION OF h_{FE2}

RANK	C	D	E
RANGE	120-200	160-300	250-500

TYPICAL CHARACTERISTICS



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